NXP Semiconductors - MPC8323ECVRAFDCA Datasheet

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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8323ecvrafdca

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2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
DDR1 signal	18	GV_{DD} = 2.5 V
DDR2 signal	18	GV_{DD} = 1.8 V
DUART, system control, I2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V

2.1.4 Input Capacitance Specification

Table 4 describes the input capacitance for the CLKIN pin in the MPC8323E.

Table 4. Input Capacitance Specification

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input capacitance for all pins except CLKIN	C_I	6	8	pF	—
Input capacitance for CLKIN	C_{ICLKIN}	10	—	pF	1

Note:
1. The external clock generator should be able to drive 10 pF.

2.2 Power Sequencing

The device does not require the core supply voltage (V_{DD}) and IO supply voltages (GV_{DD} and OV_{DD}) to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating $\overline{\text{PORESET}}$.

Note that there is no specific power down sequence requirement for the device. I/O voltage supplies (GV_{DD} and OV_{DD}) do not have any ordering requirements with respect to one another.

Table 7. CLKIN DC Electrical Characteristics (continued)

CLKIN input current	0 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	0 V ≤ V_{IN} ≤ 0.5 V or OV_{DD} – 0.5 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	±5	μA
PCI_SYNC_IN input current	0.5 V ≤ V_{IN} ≤ OV_{DD} – 0.5 V	I_{IN}	—	±50	μA

4.2 AC Electrical Characteristics

The primary clock source for the MPC8323E can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 8 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the MPC8323E.

Table 8. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	25	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN rise and fall time	t_{KH}, t_{KL}	0.6	0.8	4	ns	2
PCI_CLK rise and fall time	t_{PCH}, t_{PCL}	0.6	0.8	1.2	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, security, and QUICC Engine block must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be < 500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

5 RESET Initialization

This section describes the AC electrical specifications for the reset initialization timing requirements of the MPC8323E. Table 9 provides the reset initialization AC timing specifications for the reset component(s).

Table 9. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{PCI\_SYNC\_IN}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8323E is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the MPC8323E is in PCI agent mode	32	—	$t_{PCI\_SYNC\_IN}$	1

Table 11. Reset Signals DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input current	I_{IN}	$0\text{ V} \le V_{IN} \le OV_{DD}$	—	±5	μA	—

Note:

1. This specification applies when operating from 3.3 V supply.

6 DDR1 and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR1 and DDR2 SDRAM interface of the MPC8323E. Note that DDR1 SDRAM is Dn_GV_{DD}(typ) = 2.5 V and DDR2 SDRAM is Dn_GV_{DD}(typ) = 1.8 V. The AC electrical specifications are the same for DDR1 and DDR2 SDRAM.

6.1 DDR1 and DDR2 SDRAM DC Electrical Characteristics

Table 12 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8323E when Dn_GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM DC Electrical Characteristics for Dn_GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV_{DD}	1.71	1.89	V	1
I/O reference voltage	$MVREFn_{REF}$	$0.49 \times Dn\_GV_{DD}$	$0.51 \times Dn\_GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MVREFn_{REF} - 0.04$	$MVREFn_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MVREFn_{REF} + 0.125$	$Dn\_GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MVREFn_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	–9.9	9.9	μA	4
Output high current (V_{OUT} = 1.35 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:

1. Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.
2. $MVREFn_{REF}$ is expected to be equal to $0.5 \times Dn\_GV_{DD}$, and to track Dn_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MVREFn_{REF}$ may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to $MVREFn_{REF}$. This rail should track variations in the DC level of $MVREFn_{REF}$.
4. Output leakage is measured with all outputs disabled, $0\text{ V} \le V_{OUT} \le Dn\_GV_{DD}$.

Table 13 provides the DDR2 capacitance when Dn_GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for Dn_GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1

6.2 DDR1 and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR1 and DDR2 SDRAM interface.

6.2.1 DDR1 and DDR2 SDRAM Input AC Timing Specifications

Table 16 provides the input AC timing specifications for the DDR2 SDRAM (D*n*_GV_{DD}(typ) = 1.8 V).

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with D*n*_GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MVREF*n*$_{REF}$ – 0.25	V	—
AC input high voltage	V_{IH}	MVREF*n*$_{REF}$ + 0.25	—	V	—

Table 17 provides the input AC timing specifications for the DDR1 SDRAM (D*n*_GV_{DD}(typ) = 2.5 V).

Table 17. DDR1 SDRAM Input AC Timing Specifications for 2.5 V Interface

At recommended operating conditions with D*n*_GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MVREF*n*$_{REF}$ – 0.31	V	—
AC input high voltage	V_{IH}	MVREF*n*$_{REF}$ + 0.31	—	V	—

Table 18 provides the input AC timing specifications for the DDR1 and DDR2 SDRAM interface.

Table 18. DDR1 and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with D*n*_GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller skew for MDQS—MDQ/MDM	t_{CISKEW}			ps	1, 2
266 MHz		–750	750		
200 MHz		–1250	1250		

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm(T/4 - \text{abs}(t_{CISKEW}))$ where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8323E.

7.1 DUART DC Electrical Characteristics

Table 20 provides the DC electrical characteristics for the DUART interface of the MPC8323E.

Table 20. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V
Input current (0 V ≤ V_{IN} ≤ OV_{DD})[1]	I_{IN}	—	±5	μA

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

Table 21 provides the AC timing parameters for the DUART interface of the MPC8323E.

Table 21. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	—	2

Notes:

1. Actual attainable baud rate is limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

8 Ethernet and MII Management

This section provides the AC and DC electrical characteristics for Ethernet and MII management.

8.1 Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics

The electrical characteristics specified here apply to all MII (media independent interface) and RMII (reduced media independent interface), except MDIO (management data input/output) and MDC

Table 23. MII Transmit AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
TX_CLK data clock fall time	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 7 shows the MII transmit AC timing diagram.

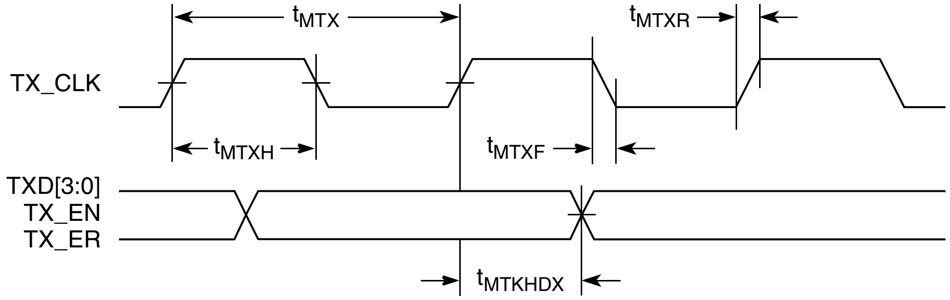


Figure 7. MII Transmit AC Timing Diagram

8.2.1.2 MII Receive AC Timing Specifications

Table 24 provides the MII receive AC timing specifications.

Table 24. MII Receive AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time	t_{MRXR}	1.0	—	4.0	ns

8.2.2.1 RMII Transmit AC Timing Specifications

Table 23 provides the RMII transmit AC timing specifications.

Table 25. RMII Transmit AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$	2	—	10	ns
REF_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 shows the RMII transmit AC timing diagram.

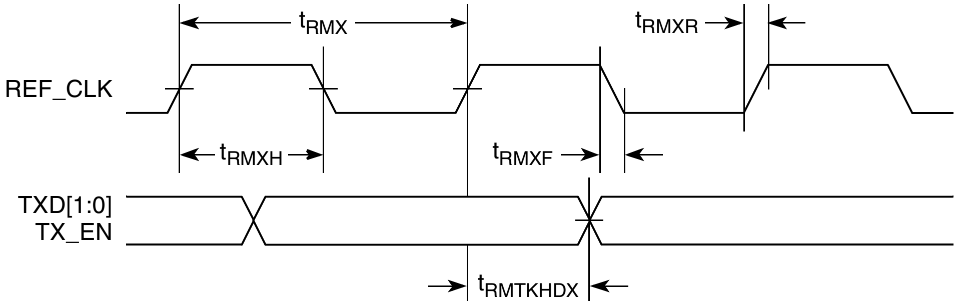


Figure 10. RMII Transmit AC Timing Diagram

8.2.2.2 RMII Receive AC Timing Specifications

Table 24 provides the RMII receive AC timing specifications.

Table 26. RMII Receive AC Timing Specifications

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
REF_CLK clock period	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	$t_{RMRDVKH}$	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	$t_{RMRDXKH}$	2.0	—	—	ns
REF_CLK clock rise V_{IL}(min) to V_{IH}(max)	t_{RMXR}	1.0	—	4.0	ns

Table 26. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
REF_CLK clock fall time V_{IH}(max) to V_{IL}(min)	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMRDVKH}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, $t_{RMRDXKL}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 provides the AC test load.

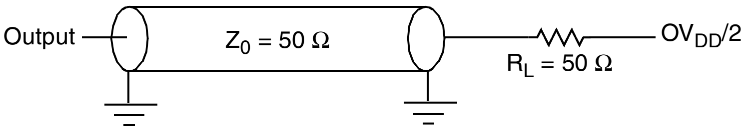


Figure 11. AC Test Load

Figure 12 shows the RMII receive AC timing diagram.

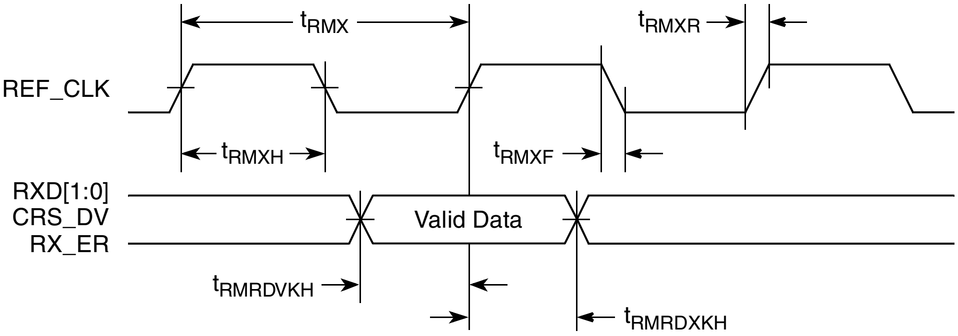


Figure 12. RMII Receive AC Timing Diagram

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, and RMII are specified in Section 8.1, “Ethernet Controller (10/100 Mbps)—MII/RMII Electrical Characteristics.”

Table 30. Local Bus General Timing Parameters (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock (LCLK*n*) to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock (LCLK*n*) to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8
Local bus clock (LCLK*n*) duty cycle	t_{LBDC}	47	53	%	—
Local bus clock (LCLK*n*) jitter specification	t_{LBRJ}	—	400	ps	—
Delay between the input clock (PCI_SYNC_IN) of local bus output clock (LCLK*n*)	t_{LBCDL}	—	1.7	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1).
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

Figure 14 provides the AC test load for the local bus.

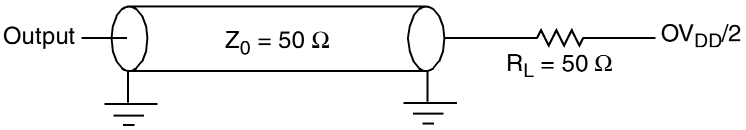
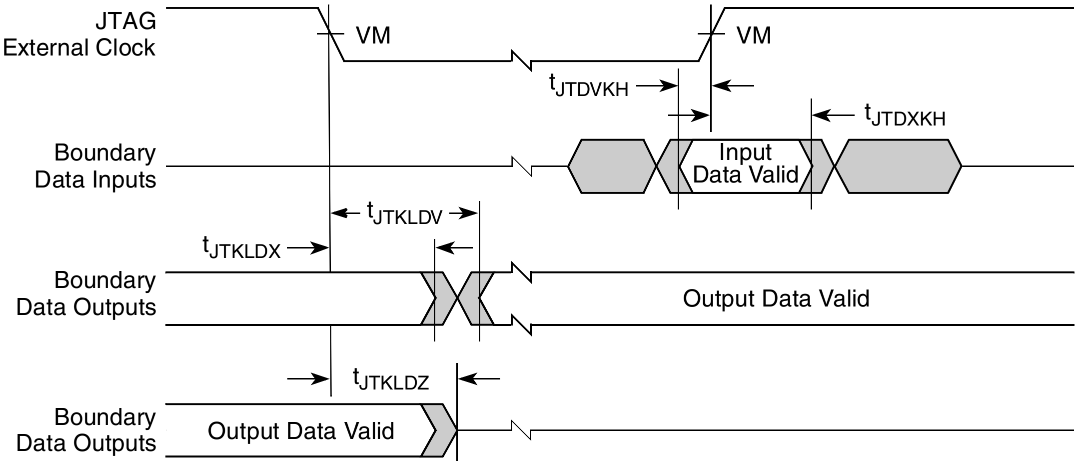


Figure 14. Local Bus C Test Load

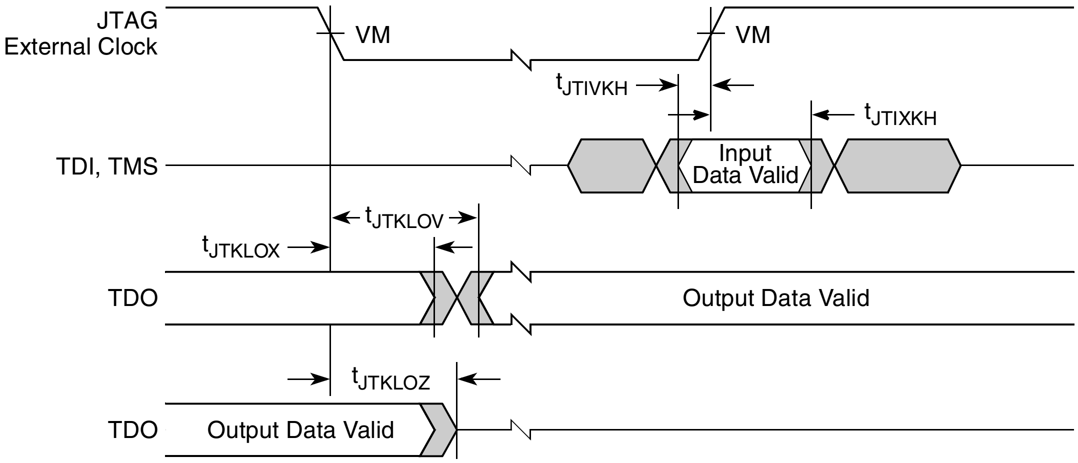
Figure 21 provides the boundary-scan timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 21. Boundary-Scan Timing Diagram

Figure 22 provides the test access port timing diagram.



VM = Midpoint Voltage ($OV_{DD}/2$)

Figure 22. Test Access Port Timing Diagram

Figure 29 provides the AC test load for the GPIO.

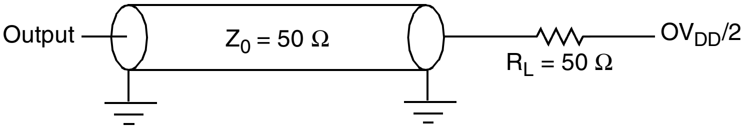


Figure 29. GPIO AC Test Load

15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8323E.

15.1 IPIC DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the external interrupt pins of the MPC8323E.

Table 42. IPIC DC Electrical Characteristics[1,2]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	µA
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:

1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, $\overline{\text{MCP\_OUT}}$, and CE ports Interrupts.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

15.2 IPIC AC Timing Specifications

Table 43 provides the IPIC input and output AC timing specifications.

Table 43. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

16 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8323E.

16.1 SPI DC Electrical Characteristics

Table 44 provides the DC electrical characteristics for the MPC8323E SPI.

Table 44. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -6.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0$ mA	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \le V_{IN} \le OV_{DD}$	—	±5	μA

16.2 SPI AC Timing Specifications

Table 45 and provide the SPI input and output AC timing specifications.

Table 45. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 30 provides the AC test load for the SPI.

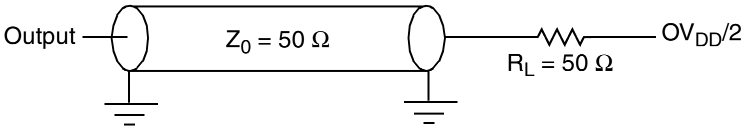


Figure 30. SPI AC Test Load

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8323E.

20.1 USB DC Electrical Characteristics

Table 53 provides the DC electrical characteristics for the USB interface.

Table 53. USB DC Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±5	µA

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

20.2 USB AC Electrical Specifications

Table 54 describes the general timing parameters of the USB interface of the MPC8323E.

Table 54. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at $OV_{DD}/2$ of the rising or falling edge of the signals.

Figure 41 provide the AC test load for the USB.

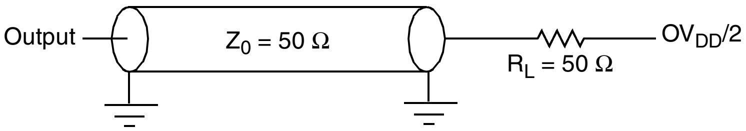


Figure 41. USB AC Test Load

21 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8323E is available in a thermally enhanced Plastic Ball Grid Array (PBGA); see Section 21.1, "Package Parameters for the MPC8323E PBGA," and Section 21.2, "Mechanical Dimensions of the MPC8323E PBGA," for information on the PBGA.

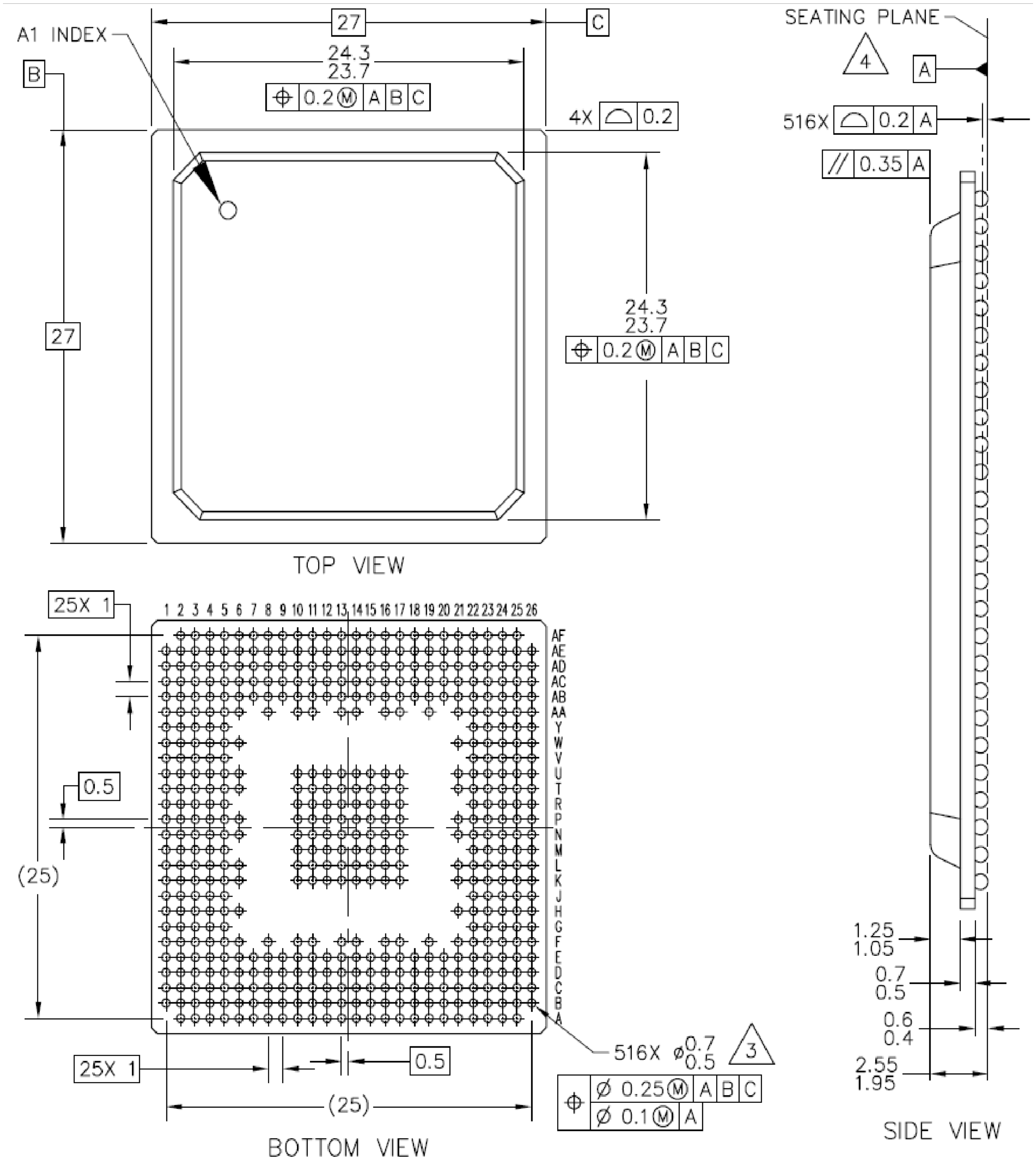
21.1 Package Parameters for the MPC8323E PBGA

The package parameters are as provided in the following list. The package type is 27 mm × 27 mm, 516 PBGA.

Package outline	27 mm × 27 mm
Interconnects	516
Pitch	1.00 mm
Module height (typical)	2.25 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZQ package) 95.5 Sn/0.5 Cu/4Ag (VR package)
Ball diameter (typical)	0.6 mm

21.2 Mechanical Dimensions of the MPC8323E PBGA

Figure 42 shows the mechanical dimensions and bottom surface nomenclature of the MPC8323E, 516-PBGA package.



Notes:

1.All dimensions are in millimeters.

2.Dimensions and tolerances per ASME Y14.5M-1994.

3.Maximum solder ball diameter measured parallel to datum A.

4.Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 42. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8323E PBGA

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MDQ29	AD20	IO	GV_{DD}	—
MEMC_MDQ30	AF23	IO	GV_{DD}	—
MEMC_MDQ31	AD22	IO	GV_{DD}	—
MEMC_MDM0	AC9	O	GV_{DD}	—
MEMC_MDM1	AD5	O	GV_{DD}	—
MEMC_MDM2	AE20	O	GV_{DD}	—
MEMC_MDM3	AE22	O	GV_{DD}	—
MEMC_MDQS0	AE8	IO	GV_{DD}	—
MEMC_MDQS1	AE5	IO	GV_{DD}	—
MEMC_MDQS2	AC19	IO	GV_{DD}	—
MEMC_MDQS3	AE23	IO	GV_{DD}	—
MEMC_MBA0	AD16	O	GV_{DD}	—
MEMC_MBA1	AD17	O	GV_{DD}	—
MEMC_MBA2	AE17	O	GV_{DD}	—
MEMC_MA0	AD12	O	GV_{DD}	—
MEMC_MA1	AE12	O	GV_{DD}	—
MEMC_MA2	AF12	O	GV_{DD}	—
MEMC_MA3	AC13	O	GV_{DD}	—
MEMC_MA4	AD13	O	GV_{DD}	—
MEMC_MA5	AE13	O	GV_{DD}	—
MEMC_MA6	AF13	O	GV_{DD}	—
MEMC_MA7	AC15	O	GV_{DD}	—
MEMC_MA8	AD15	O	GV_{DD}	—
MEMC_MA9	AE15	O	GV_{DD}	—
MEMC_MA10	AF15	O	GV_{DD}	—
MEMC_MA11	AE16	O	GV_{DD}	—
MEMC_MA12	AF16	O	GV_{DD}	—
MEMC_MA13	AB16	O	GV_{DD}	—
$\overline{\text{MEMC\_MWE}}$	AC17	O	GV_{DD}	—
$\overline{\text{MEMC\_MRAS}}$	AE11	O	GV_{DD}	—
$\overline{\text{MEMC\_MCAS}}$	AD11	O	GV_{DD}	—
$\overline{\text{MEMC\_MCS}}$	AC11	O	GV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PB17/BRGO1/CE_EXT_REQ1	D10	IO	OV_{DD}	—
GPIO_PB18/Enet4_TXD[0]/SER4_TXD[0]/ TDMD_TXD[0]	C10	IO	OV_{DD}	—
GPIO_PB19/Enet4_TXD[1]/SER4_TXD[1]/ TDMD_TXD[1]	C9	IO	OV_{DD}	—
GPIO_PB20/Enet4_TXD[2]/SER4_TXD[2]/ TDMD_TXD[2]	D8	IO	OV_{DD}	—
GPIO_PB21/Enet4_TXD[3]/SER4_TXD[3]/ TDMD_TXD[3]	C8	IO	OV_{DD}	—
GPIO_PB22/Enet4_RXD[0]/SER4_RXD[0]/ TDMD_RXD[0]	C15	IO	OV_{DD}	—
GPIO_PB23/Enet4_RXD[1]/SER4_RXD[1]/ TDMD_RXD[1]	C14	IO	OV_{DD}	—
GPIO_PB24/Enet4_RXD[2]/SER4_RXD[2]/ TDMD_RXD[2]	D13	IO	OV_{DD}	—
GPIO_PB25/Enet4_RXD[3]/SER4_RXD[3]/ TDMD_RXD[3]	C13	IO	OV_{DD}	—
GPIO_PB26/Enet4_RX_ER/SER4_CD/TDMD_REQ	C12	IO	OV_{DD}	—
GPIO_PB27/Enet4_TX_ER/TDMD_CLKO	D11	IO	OV_{DD}	—
GPIO_PB28/Enet4_RX_DV/SER4_CTS/ TDMD_RSYNC	D12	IO	OV_{DD}	—
GPIO_PB29/Enet4_COL/RXD[4]/SER4_RXD[4]/ TDMD_STROBE	D7	IO	OV_{DD}	—
GPIO_PB30/Enet4_TX_EN/SER4_RTS/ TDMD_TSYNC	C11	IO	OV_{DD}	—
GPIO_PB31/Enet4_CRS/SDET	C7	IO	OV_{DD}	—
GPIO_PC0/UPC1_TxDATA[0]/SER5_TXD[0]	A18	IO	OV_{DD}	—
GPIO_PC1/UPC1_TxDATA[1]/SER5_TXD[1]	A19	IO	OV_{DD}	—
GPIO_PC2/UPC1_TxDATA[2]/SER5_TXD[2]	B18	IO	OV_{DD}	—
GPIO_PC3/UPC1_TxDATA[3]/SER5_TXD[3]	B19	IO	OV_{DD}	—
GPIO_PC4/UPC1_TxDATA[4]	A24	IO	OV_{DD}	—
GPIO_PC5/UPC1_TxDATA[5]	B24	IO	OV_{DD}	—
GPIO_PC6/UPC1_TxDATA[6]	A23	IO	OV_{DD}	—
GPIO_PC7/UPC1_TxDATA[7]	B26	IO	OV_{DD}	—
GPIO_PC8/UPC1_RxDATA[0]/SER5_RXD[0]	A21	IO	OV_{DD}	—
GPIO_PC9/UPC1_RxDATA[1]/SER5_RXD[1]	B20	IO	OV_{DD}	—

Table 57. Operating Frequencies for PBGA (continued)

Characteristic[1]	Max Operating Frequency	Unit
DDR1/DDR2 memory bus frequency (MCLK)[2]	133	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz
PCI input frequency (CLKIN or PCI_CLK)	66	MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.

[2] The DDR1/DDR2 data rate is 2× the DDR1/DDR2 memory bus frequency.

[3] The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

22.4 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 58 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider).

The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 300–600 MHz.

Table 58. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

As described in Section 22, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the $\overline{\text{CFG\_CLKIN\_DIV}}$ configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59 shows the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 59. CSB Frequency Options

CFG_CLKIN_DIV_B at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio [2]	Input Clock Frequency (MHz)[2]		
			25	33.33	66.67
			csb_clk Frequency (MHz)		
High	0010	2 : 1			133
High	0011	3 : 1		100	
High	0100	4 : 1	100	133	
High	0101	5 : 1	125		
High	0110	6 : 1			
High	0111	7 : 1			
High	1000	8 : 1			
High	1001	9 : 1			
High	1010	10 : 1			
High	1011	11 : 1			
High	1100	12 : 1			
High	1101	13 : 1			
High	1110	14 : 1			
High	1111	15 : 1			
High	0000	16 : 1			
Low	0010	2 : 1			133
Low	0011	3 : 1		100	
Low	0100	4 : 1		133	
Low	0101	5 : 1			
Low	0110	6 : 1			
Low	0111	7 : 1			
Low	1000	8 : 1			
Low	1001	9 : 1			
Low	1010	10 : 1			
Low	1011	11 : 1			
Low	1100	12 : 1			
Low	1101	13 : 1			
Low	1110	14 : 1			
Low	1111	15 : 1			
Low	0000	16 : 1			

[1] CFG_CLKIN_DIV_B is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV_B must be pulled up (high) in agent mode.

[2] CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

22.6 QUICC Engine PLL Configuration

The QUICC Engine PLL is controlled by the RCWL[CEPMF] and RCWL[CEPDF] parameters. Table 61 shows the multiplication factor encodings for the QUICC Engine PLL.

Table 61. QUICC Engine PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF)
00000–00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001–11111	0	Reserved

The RCWL[CEVCOD] denotes the QUICC Engine PLL VCO internal frequency as shown in Table 62.

Table 62. QUICC Engine PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine VCO frequency is in the range of 300–600 MHz. The QUICC Engine frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine frequencies should be selected according to the performance requirements.

The QUICC Engine VCO frequency is derived from the following equations:

$$\mathit{ce\_clk} = (\text{primary clock input} \times \text{CEPMF}) \div (1 + \text{CEPDF})$$

$$\text{QUICC Engine VCO Frequency} = \mathit{ce\_clk} \times \text{VCO divider} \times (1 + \text{CEPDF})$$